

### Description

The LMTL3N06 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

### General Features

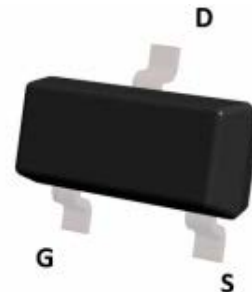
$V_{DS} = 60V$   $I_D = 3A$

$R_{DS(ON)} < 100m\Omega$  @  $V_{GS}=10V$

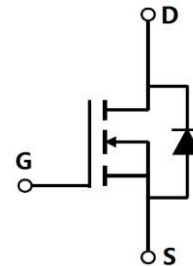
### Application

- Battery protection
- Load switch
- Uninterruptible power supply

### Dimensions SOT-23



### Pin Configuration



### Package Marking and Ordering Information

Device	Device Marking	Device Package	Reel Size	Tape width	Quantity
LMTL3N06	6003	SOT-23	-	-	3000 units

### Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	3.0	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	1.8	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	9.2	A
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>3</sup>	1	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	125	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	80	°C/W

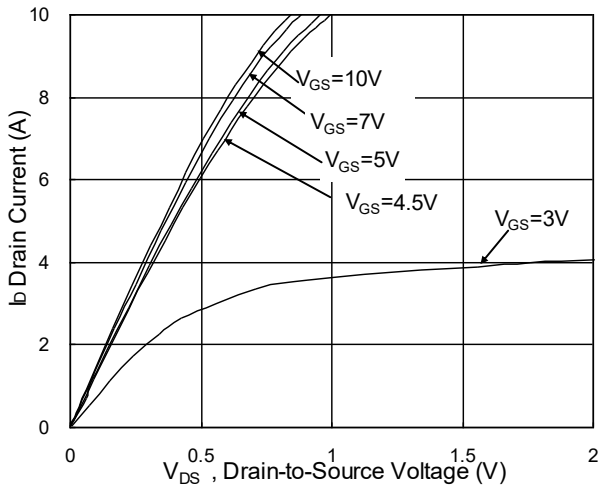
**Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.054	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =2A	---	80	100	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =1A	---	85	110	
V <sub>GS(th)</sub>	Gate Threshold Voltage		1.2	---	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250μA	---	-4.96	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	μA
		V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =2A	---	13	---	S
Q <sub>g</sub>	Total Gate Charge (4.5V)		---	5	7.0	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =48V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A	---	1.68	2.4	
Q <sub>gd</sub>	Gate-Drain Charge		---	1.9	2.7	
T <sub>d(on)</sub>	Turn-On Delay Time		---	1.6	3.2	ns
T <sub>r</sub>	Rise Time	V <sub>DD</sub> =30V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =2A	---	7.2	13	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	25	50	
T <sub>f</sub>	Fall Time		---	14.4	28.8	
C <sub>iss</sub>	Input Capacitance		---	511	715	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	38	53	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	25	35	
I <sub>S</sub>	Continuous Source Current <sup>1,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	2.3	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,4</sup>		---	---	9.2	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =2A, di/dt=100A/μs, T <sub>J</sub> =25°C	---	9.7	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	5.8	---	nC

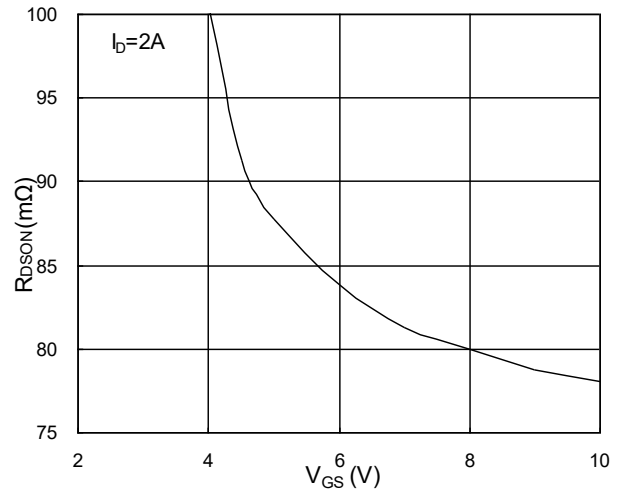
Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature.
- 4.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

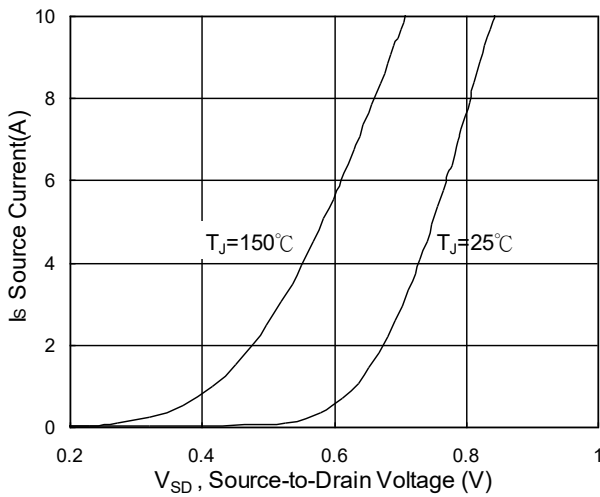
**Typical Characteristics**



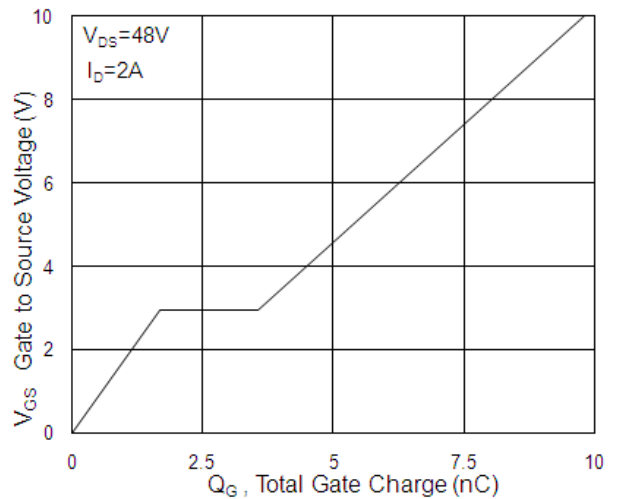
**Fig.1 Typical Output Characteristics**



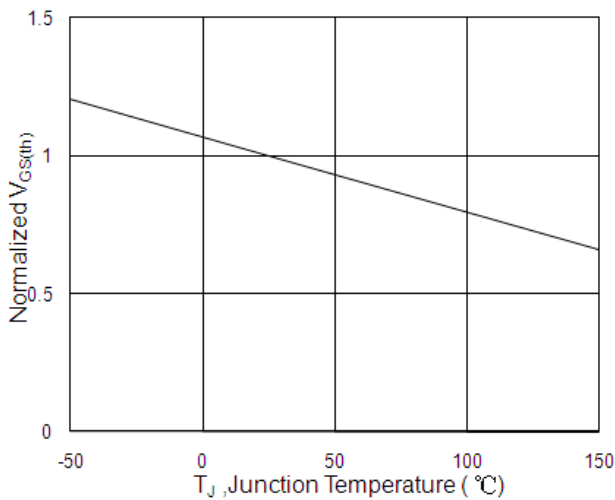
**Fig.2 On-Resistance v.s Gate-Source**



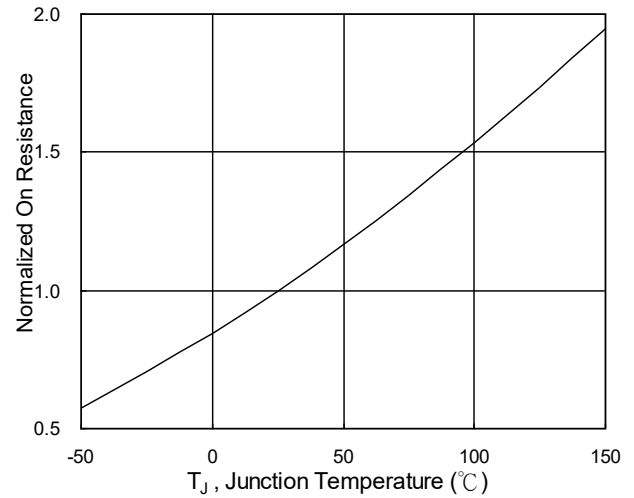
**Fig.3 Forward Characteristics of Reverse**



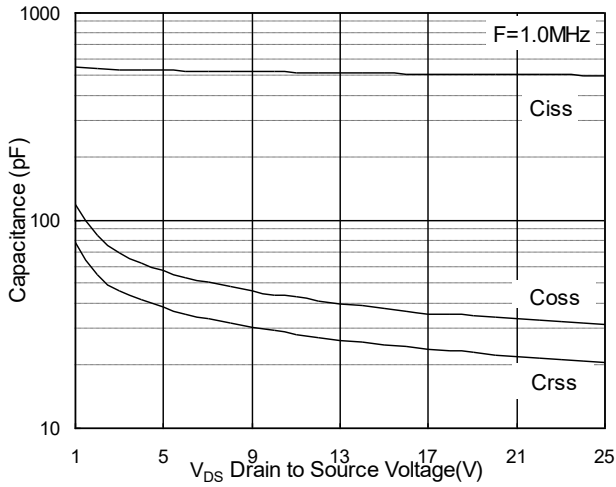
**Fig.4 Gate-Charge Characteristics**



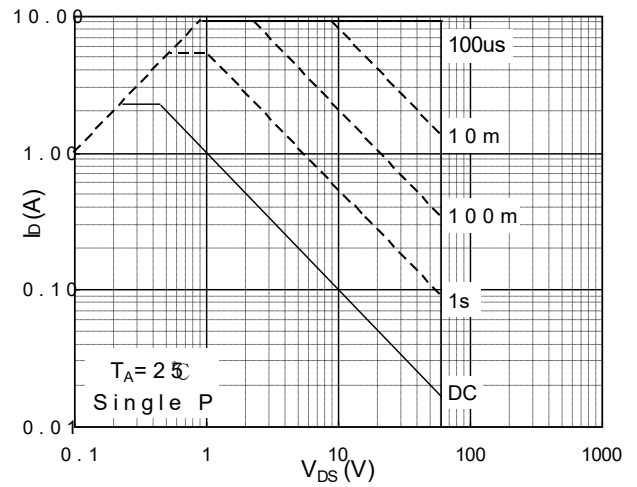
**Fig.5 Normalized  $V_{GS(th)}$  v.s  $T_J$**



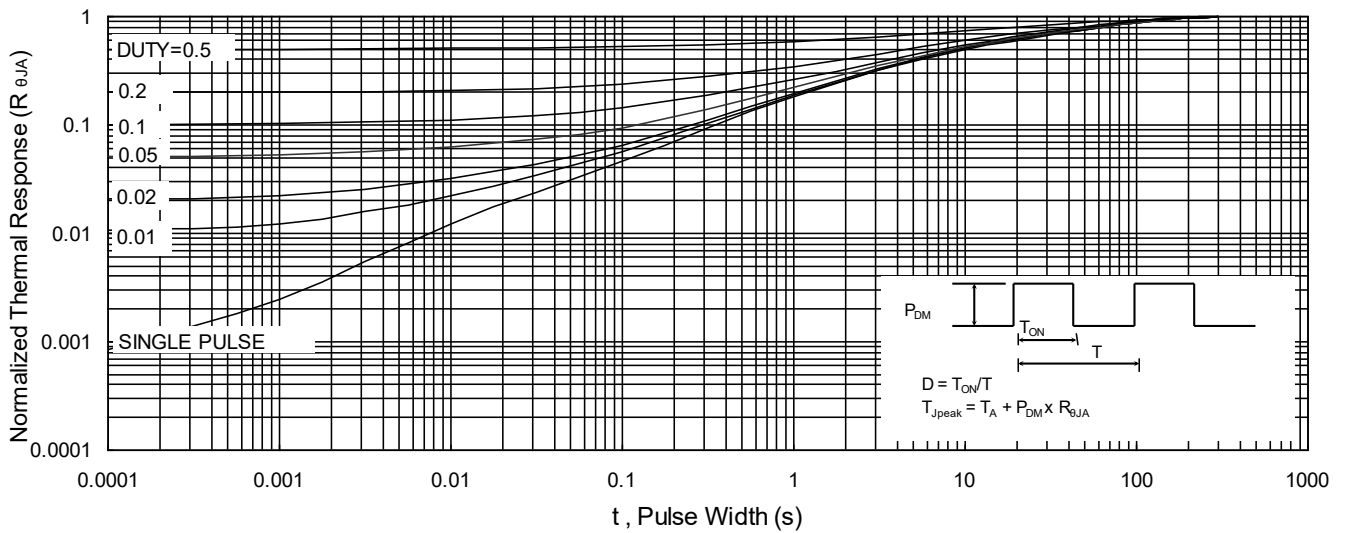
**Fig.6 Normalized  $R_{DS(on)}$  v.s  $T_J$**



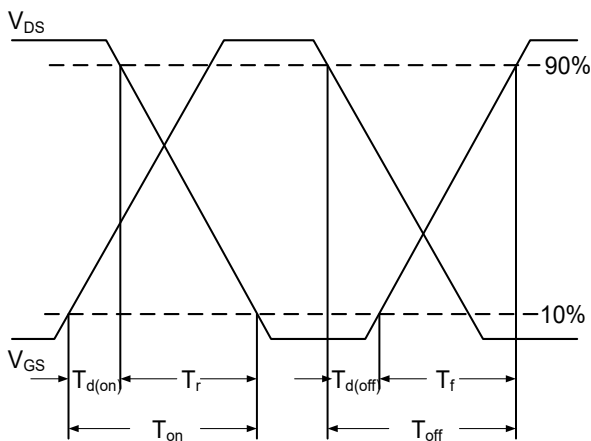
**Fig.7 Capacitance**



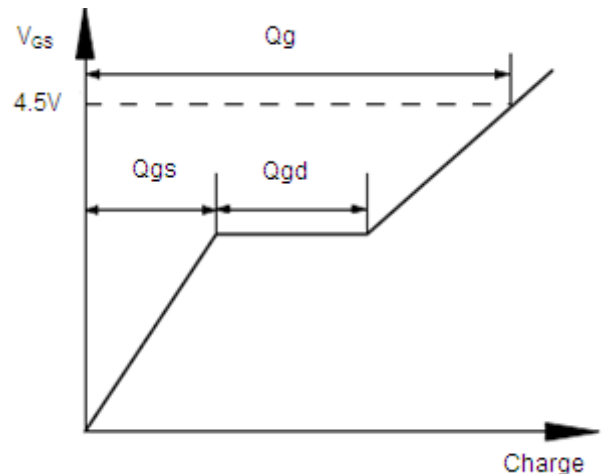
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**

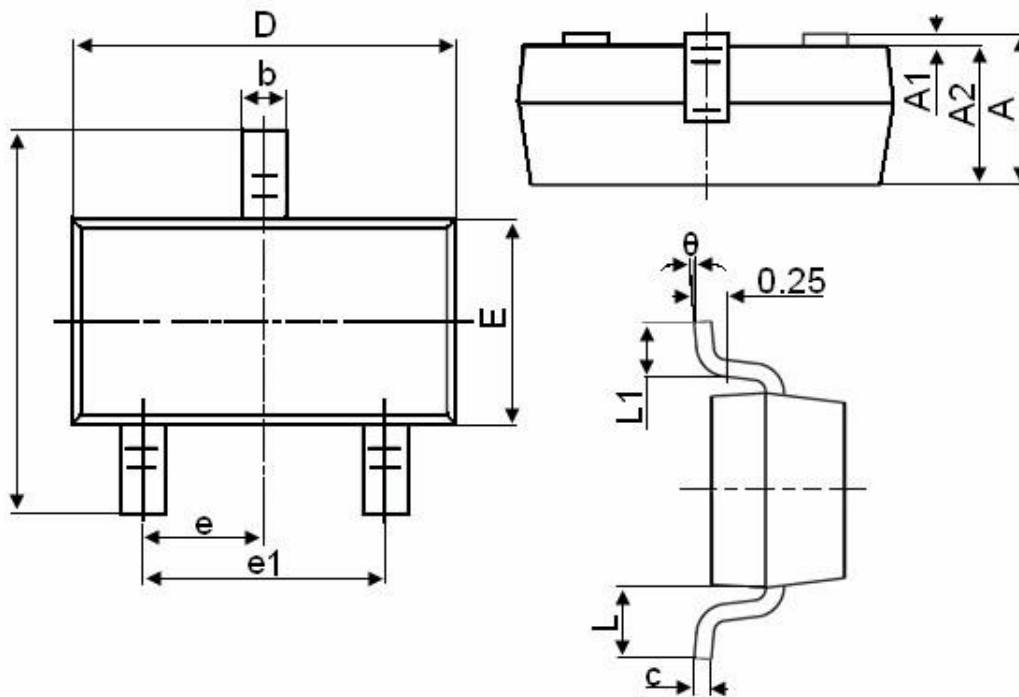


**Fig.10 Switching Time Waveform**



**Fig.11 Gate Charge Waveform**

Package Mechanical Data-SOT-23



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
$\theta$	0°	8°